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September 2014

# H11L1M, H11L2M, H11L3M 6-Pin DIP Schmitt Trigger Output Optocoupler

### **Features**

- High Data Rate, 1 MHz Typical (NRZ)
- Free from Latch-up and Oscilliation Throughout Voltage and Temperature Ranges
- Microprocessor Compatible Drive
- Logic Compatible Output Sinks 16 mA at 0.4 V Maximum
- Guaranteed On/Off Threshold Hysteresis
- Wide Supply Voltage Capability, Compatible with All Popular Logic Systems
- Safety and Regulatory Approvals:
  - UL1577, 4,170 VAC<sub>RMS</sub> for 1 Minute
  - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

# **Applications**

- Logic-to-Logic Isolator
- Programmable Current Level Sensor
- Line Receiver—Eliminate Noise and Transient Problems
- AC to TTL Conversion—Square Wave Shaping
- Digital Programming of Power Supplies
- Interfaces Computers with Peripherals

### **Description**

The H11LXM series has a high-speed integrated circuit detector optically coupled to a gallium-arsenide infrared emitting diode. The output incorporates a Schmitt trigger, which provides hysteresis for noise immunity and pulse shaping. The detector circuit is optimized for simplicity of operation and utilizes an open-collector output for maximum application flexibility.

### **Schematic**

# ANODE 1 CATHODE 2 5 GND Truth Table Input Output 4 Vo H L L H

Figure 1. Schematic

### **Package Outlines**

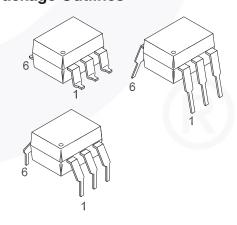


Figure 2. Package Outlines

# **Safety and Insulation Ratings**

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
\/	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, V <sub>IORM</sub> x 1.875 = V <sub>PR</sub> , 100% Production Test with t <sub>m</sub> = 1 s, Partial Discharge < 5 pC	1594	V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	850	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
T <sub>S</sub>	Case Temperature <sup>(1)</sup>	175	°C
I <sub>S,INPUT</sub>	Input Current <sup>(1)</sup>	350	mA
P <sub>S,OUTPUT</sub>	Output Power <sup>(1)</sup>	800	mW
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V <sup>(1)</sup>	> 10 <sup>9</sup>	Ω

### Note:

1. Safety limit values – maximum values allowed in the event of a failure.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Parameters	Value	Units
Total Device			
T <sub>STG</sub>	Storage Temperature	-40 to +125	°C
T <sub>OPR</sub>	Operating Temperature	-40 to +85	°C
TJ	Junction Temperature	-40 to +125	°C
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 seconds	°C
P <sub>D</sub>	Total Device Power Dissipation at 25°C	250	mW
	Derate Above 25°C	2.94	mW/°C
mitter			
I <sub>F</sub>	Continuous Forward Current	30	mA
$V_{R}$	Reverse Voltage	6	V
I <sub>F</sub> (pk)	Forward Current – Peak (1 µs pulse, 300 pps)	100	mA
P <sub>D</sub>	LED Power Dissipation	60	mW
Detector	•		
$P_{D}$	Detector Power Dissipation	150	mW
Vo	V <sub>45</sub> Allowed Range	0 to 16	V
V <sub>CC</sub>	V <sub>65</sub> Allowed Range	3 to 16	V
Io	I <sub>4</sub> Output Current	50	mA

### **Electrical Characteristics**

 $T_A = 25$ °C unless otherwise specified.

### **Individual Component Characteristics**

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Units
Emitter						•	
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 10 mA	All		1.2	1.5	V
		$I_F = 0.3 \text{ mA}$		0.75	1.0		
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 3 V	All			10	μA
CJ	Capacitance	V = 0, f = 1.0 MHz	All			100	pF
Detector	Detector						
V <sub>CC</sub>	Operating Voltage Range		All	3		15	V
I <sub>CC(off)</sub>	Supply Current	$I_F = 0, V_{CC} = 5 V$	All		1.6	5.0	mA
I <sub>OH</sub>	Output Current, High	$I_F = 0, V_{CC} = V_O = 15 \text{ V}$	All			100	μA

### **Transfer Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Тур.	Max.	Units
DC Charac	teristics				1		
I <sub>CC(on)</sub>	Supply Current	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}$	All		1.6	5.0	mA
V <sub>OL</sub>	Output Voltage, Low	$R_L = 270 \Omega, V_{CC} = 5 V,$ $I_F = I_{F(on)} \text{ max.}$	All		0.2	0.4	V
I <sub>F(on)</sub>	Turn-On Threshold Current <sup>(2)</sup>	$R_L = 270 \Omega, V_{CC} = 5 V$	H11L1M			1.6	mA
			H11L2M			10.0	
			H11L3M			5.0	
I <sub>F(off)</sub>	Turn-Off Threshold Current	$R_L = 270 \ \Omega, V_{CC} = 5 \ V$	All	0.3	1.0		mA
I <sub>F(off)</sub> /I <sub>F(on)</sub>	Hysteresis Ratio	$R_L = 270 \Omega, V_{CC} = 5 V$	All	0.50	0.75	0.90	
AC Charact	teristics, Switching Speed		,				
t <sub>on</sub>	Turn-On Time	$R_L = 270 \Omega, V_{CC} = 5 V,$ $I_F = I_{F(on)}, T_A = 25^{\circ}C$	All		1.0	4.0	μs
t <sub>f</sub>	Fall Time	$R_L = 270 \Omega, V_{CC} = 5 V,$ $I_F = I_{F(on)}, T_A = 25^{\circ}C$	All		0.1	y	μs
t <sub>off</sub>	Turn-Off Time	$R_L = 270 \Omega, V_{CC} = 5 V,$ $I_F = I_{F(on)}, T_A = 25^{\circ}C$	All		1.2	4.0	μs
t <sub>r</sub>	Rise Time	$R_L = 270 \Omega, V_{CC} = 5 V,$ $I_F = I_{F(on)}, T_A = 25^{\circ}C$	All		0.1		μs
	Data Rate		All		1.0		MHz

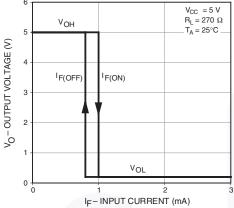
### **Isolation Characteristics**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
V <sub>ISO</sub>	Input-Output Isolation Voltage	t = 1 Minute	4170			VAC <sub>RMS</sub>
C <sub>ISO</sub>	Isolation Capacitance	V <sub>I-O</sub> = 0 V, f = 1 MHz		0.4	0.6	pF
R <sub>ISO</sub>	Isolation Resistance	$V_{I-O} = \pm 500 \text{ VDC}, T_A = 25^{\circ}\text{C}$	10 <sup>11</sup>			Ω

### Note:

<sup>2.</sup> Maximum I<sub>F(ON)</sub> is the maximum current required to trigger the output. For example, a 1.6 mA maximum trigger current would require the LED to be driven at a current greater than 1.6 mA to guarantee the device turns on. A 10% guard band is recommended to account for degradation of the LED over its lifetime. The maximum allowable LED drive current is 30 mA.

# **Typical Performance Curves**



**Figure 3. Transfer Characteristics** 

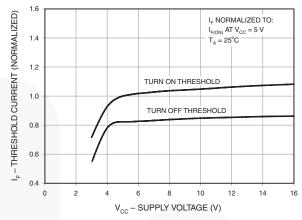


Figure 4. Threshold Current vs. Supply Voltage

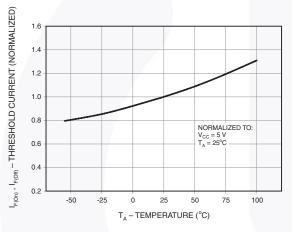


Figure 5. Threshold Current vs. Supply Temperature

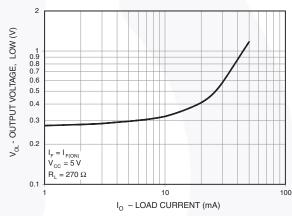


Figure 6. Output Voltage, Low vs. Load Current

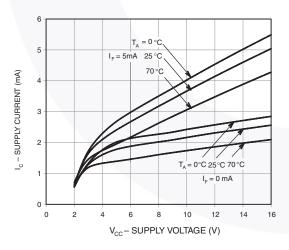


Figure 7. Supply Current vs. Supply Voltage

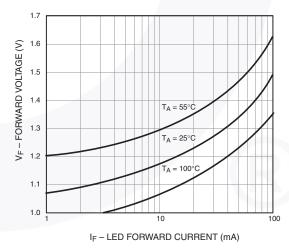


Figure 8. LED Forward Voltage vs. Forward Current

# **Typical Performance Curves** (Continued)

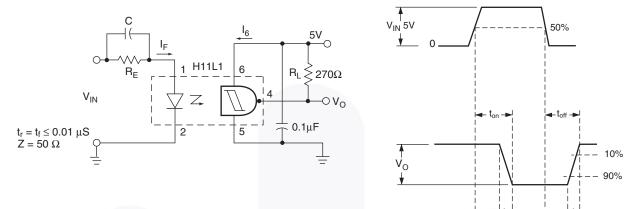


Figure 9. Switching Test Circuit and Waveforms

# **Reflow Profile**

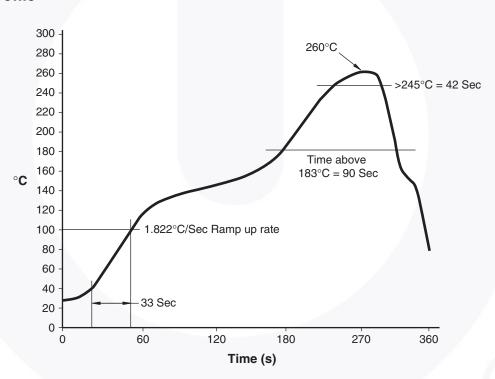


Figure 10. Reflow Profile

# **Ordering Information**

Part Number	Package	Packing Method
H11L1M	DIP 6-Pin	Tube (50 Units)
H11L1SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
H11L1SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
H11L1VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
H11L1SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
H11L1SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
H11L1TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

### Note:

3. The product orderable part number system listed in this table also applies to the H11L2M and H11L3M product families.

# **Marking Information**

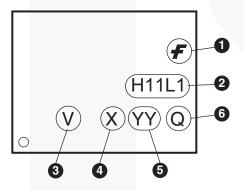
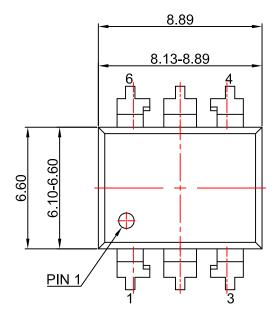
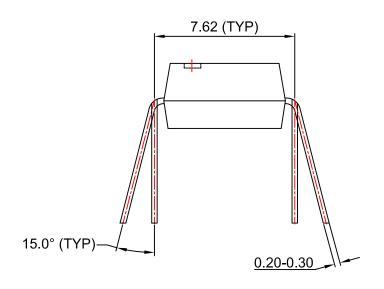


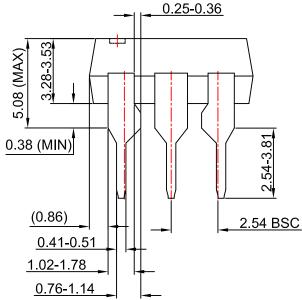
Figure 11. Top Mark

### **Table 1. Top Mark Definitions**

1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "4"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code



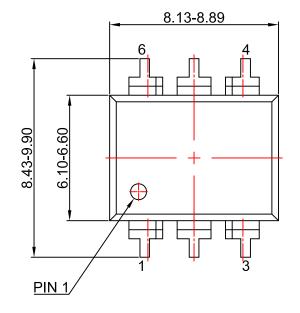


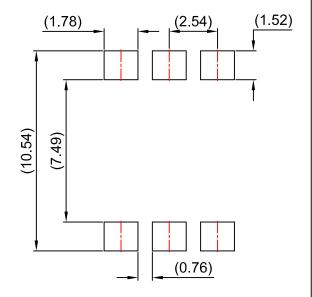


### NOTES:

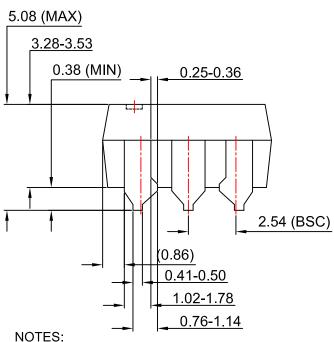
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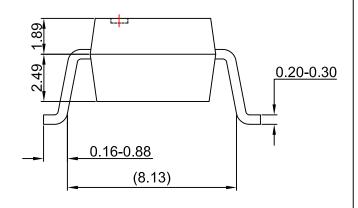






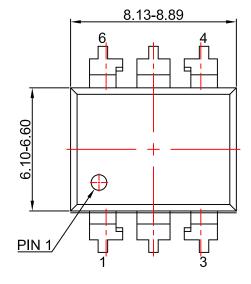
LAND PATTERN RECOMMENDATION

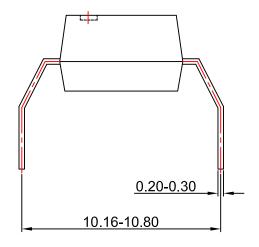


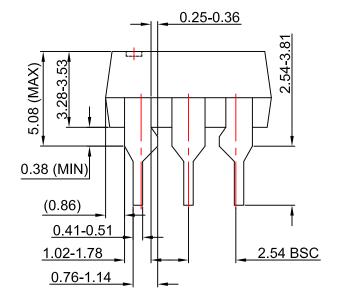


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